

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S10	22	(method and semiconductor and device and form and first and second and gate and electrode and (insulat\$3 or dielectric) and (layer or film) and source and drain and organic and material and etch).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/09 13:20
S11	1	("6278127").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/01/10 13:29

1/ 19/ 2010 9:59:32 AM**C:\ Documents and Settings\ aho1\ My Documents\ EAST\ Workspaces\ 10573328.wsp**